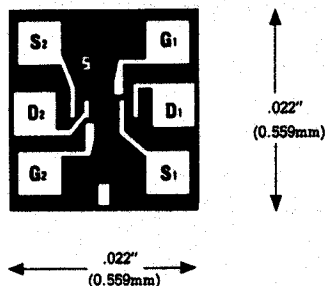


CHIP NUMBER
DMN2.4



Die Size: 22 x 22 (mils)
0.569 x 0.569(mm)
4 x 4 (mils)
Pad Size: 0.102 x 0.102(mm)

CONTACT METALLIZATION

Top Contact: > 12,000
Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

It is advisable that:

- the die be eutectically mounted with gold silicon preform 98/2%.
- 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

TYPICAL ELECTRICAL CHARACTERISTICS

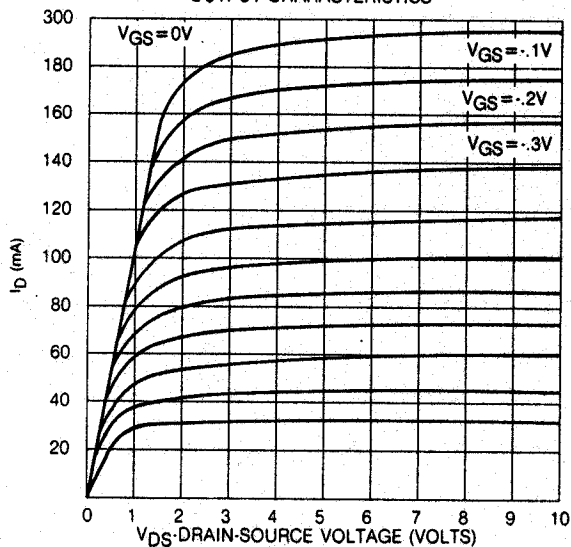
PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BVGSS	- 40	-55	- 60	V	$V_{DS} = 0, I_G = -1\mu A$
I_{GSS}		0.2	5	pA	$V_{DS} = 0, V_{GS} = -20V$
I_{DSS}	30		500	μA	$V_{DS} = 10V, V_{GS} = 0$
V_p	- 0.6		- 4.5	V	$V_{DS} = 10, I_D = 1nA$
g_{fs}	70	200	350	μS	$V_{DS} = 10V, V_{GS} = 0, F = 1KHz$
C_{iss}		2.8	3.5	pF	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$
C_{rss}		0.7	1.5	pF	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$
Y_{os}		.02	1.0	μS	$V_{DS} = 10V, I_D = 30\mu A, 1KHz$

TYPICAL DEVICE TYPES: 2N5902 - 2N5909

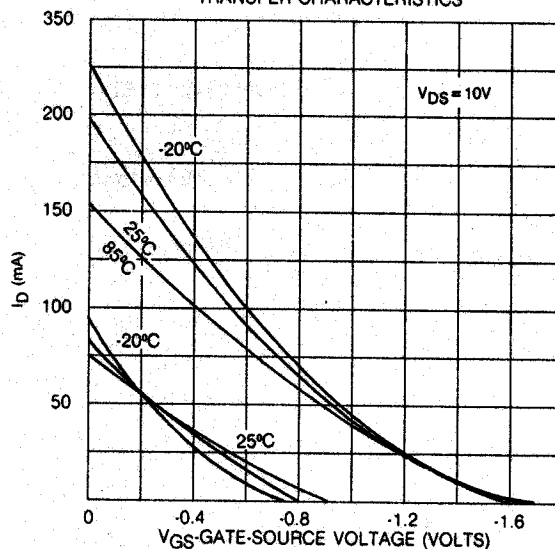
N-CHANNEL DUAL JUNCTION FET

CHIP TYPE DMN2.4

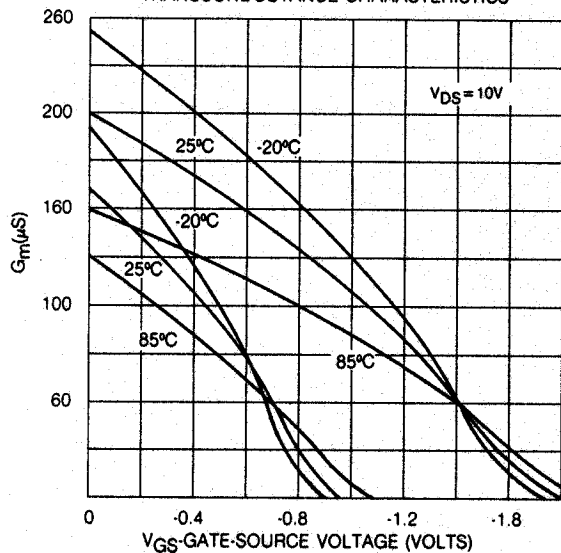
OUTPUT CHARACTERISTICS



TRANSFER CHARACTERISTICS



TRANSCONDUCTANCE CHARACTERISTICS



FORWARD TRANSCONDUCTANCE

